



### P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> T <sub>C</sub> = +25°C	
-40V	11mΩ @ V <sub>GS</sub> = -10V	-74A	
- <del>4</del> 0 V	19mΩ @ $V_{GS} = -4.5V$	-55A	

## Description

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power Management Functions
- Backlighting

# **Features and Benefits**

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMP4011SK3Q</u>)

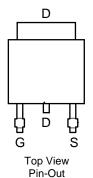
### **Mechanical Data**

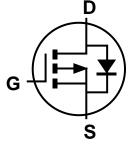
- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)

TO252 (DPAK)



Top View





**Equivalent Circuit** 

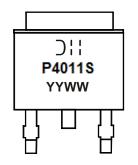
### Ordering Information (Note 4)

Part Number	Case	Packaging
DMP4011SK3-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



DII = Manufacturer's Marking P4011S = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 19 = 2019) WW = Week (01 to 53)



# **Maximum Ratings** (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	-40	V		
Gate-Source Voltage	V <sub>GSS</sub>	±20	V		
Continuous Drain Convent (Nata C) V	Steady State	$T_C = +25$ °C $T_C = +70$ °C	I <sub>D</sub>	-74 -59	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-14 -11	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-200	Α		
Maximum Body Diode Forward Current (Note 6)	I <sub>S</sub>	-70	Α		
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%	I <sub>SM</sub>	-200	Α		
Avalanche Current, L = 1mH (Note 7)	I <sub>AS</sub>	-22	Α		
Avalanche Energy, L = 1mH (Note 7)	E <sub>AS</sub>	250	mJ		

# Thermal Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		$P_D$	1.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	84	°C/W
Total Power Dissipation (Note 6)		$P_{D}$	3.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	41	°C/W
Thermal Resistance, Junction to Case		$R_{\theta JC}$	1.4	C/VV
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

# Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-40	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1	μΑ	$V_{DS} = -32V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	-2.0	-2.5	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	J	_	6.5	11	mΩ	$V_{GS} = -10V, I_D = -9.8A$	
Static Dialif-Source Off-Resistance	R <sub>DS(ON)</sub>	_	10.8	19	1115.2	$V_{GS} = -4.5V, I_D = -9.8A$	
Diode Forward Voltage	$V_{SD}$	_	-0.7	-1	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	_	2747	_		$V_{DS}$ = -20V, $V_{GS}$ = 0V f = 1MHz	
Output Capacitance	Coss	_	508	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	222	_			
Gate Resistance	$R_g$	_	21.4	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	$Q_{g}$	_	25	_			
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg	_	52	_	nC	$V_{DS} = -20V$ ,	
Gate-Source Charge	$Q_{gs}$	_	8.5	_	110	$I_D = -9.8A$	
Gate-Drain Charge	$Q_{gd}$	_	11.8	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	6.6	_			
Turn-On Rise Time	t <sub>R</sub>	_	6.5	_		$V_{GS}$ = -10V, $V_{DD}$ = -20V, $R_G$ = 6 $\Omega$ , $I_D$ = -1A	
Turn-Off Delay Time	t <sub>D(OFF)</sub>		222	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	138	_			
Reverse Recovery Time	t <sub>RR</sub>		25	_	ns	$I_F = -9.8A$ , $di/dt = -100A/\mu s$	
Reverse Recovery Charge	Q <sub>RR</sub>	_	17	_	nC	$I_F = -9.8A$ , $di/dt = -100A/\mu s$	

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

7.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_{J}$  = +25°C.

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.



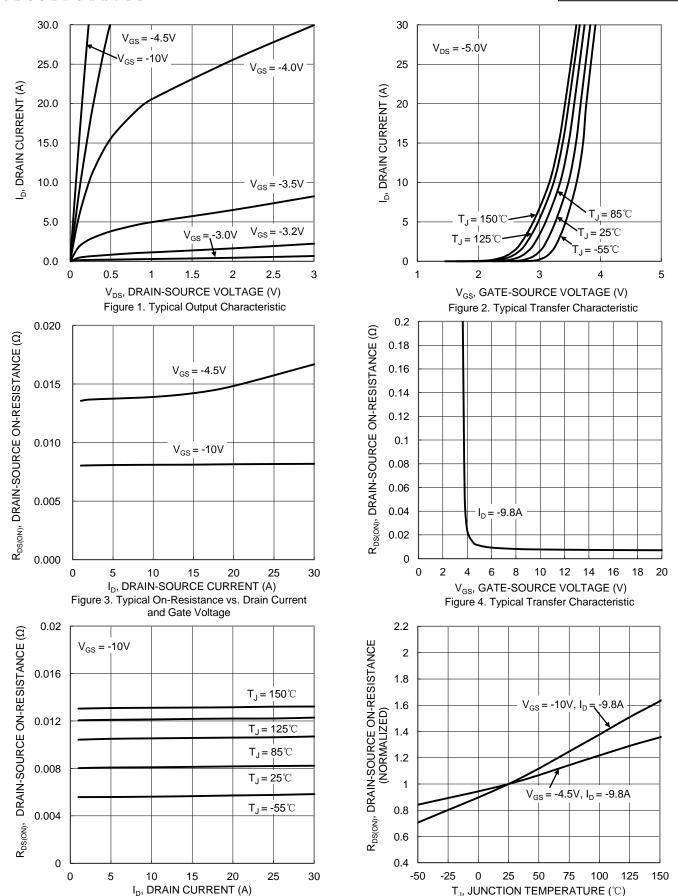


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

Figure 6. On-Resistance Variation with

Temperature



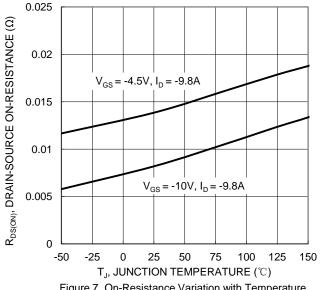


Figure 7. On-Resistance Variation with Temperature

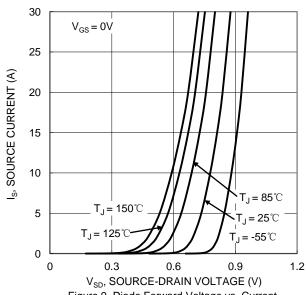


Figure 9. Diode Forward Voltage vs. Current 10 8 6  $V_{GS}(V)$ 4  $V_{DS} = -20V, I_{D} = -9.8A$ 2 0 0 5 10 15 20 25 30 35 40 45 50 55 60  $Q_q$  (nC)

Figure 11. Gate Charge

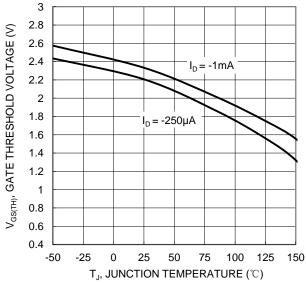
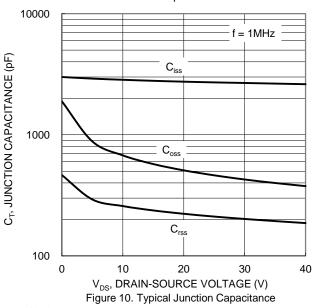
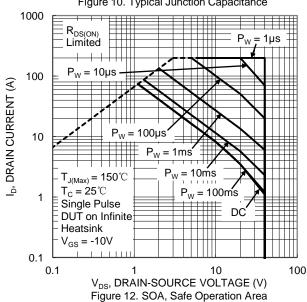


Figure 8. Gate Threshold Variation vs. Junction Temperature





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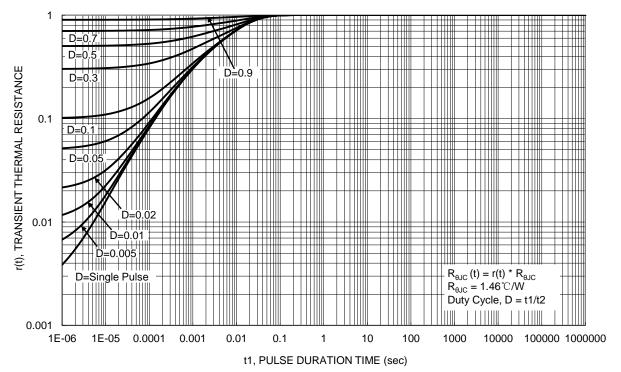


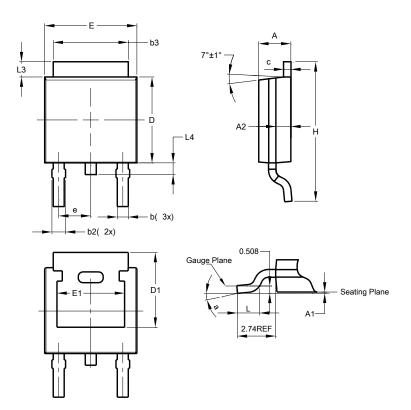
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### TO252 (DPAK)

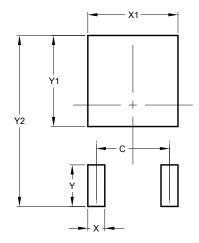


TO252 (DPAK)						
Dim	Min	Max	Тур			
Α	2.19	2.39	2.29			
<b>A</b> 1	0.00	0.13	0.08			
A2	0.97	1.17	1.07			
b	0.64	0.88	0.783			
b2	0.76	1.14	0.95			
b3	5.21	5.46	5.33			
С	0.45	0.58	0.531			
D	6.00	6.20	6.10			
D1	5.21	-	-			
е	-	-	2.286			
П	6.45	6.70	6.58			
E1	4.32	-	-			
Н	9.40	10.41	9.91			
L	1.40	1.78	1.59			
L3	0.88	1.27	1.08			
L4	0.64	1.02	0.83			
а	0°	10°	-			
All Dimensions in mm						

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

### TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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